

International IOR Rectifier

REPETITIVE AVALANCHE AND dv/dt RATED HEXFET® TRANSISTOR

IRHNA9064

P-CHANNEL RADHARD

-60Volt, 0.055 Ω , RAD HARD HEXFET

International Rectifier's P-Channel RAD HARD technology HEXFETs demonstrate excellent threshold voltage stability and breakdown voltage stability at total radiation doses as high as 10^5 Rads (Si). Under **identical** pre- and post-radiation test conditions, International Rectifier's P-Channel RAD HARD HEXFETs retain **identical** electrical specifications up to 1×10^5 Rads (Si) total dose. No compensation in gate drive circuitry is required. These devices are also capable of surviving transient ionization pulses as high as 1×10^{12} Rads (Si)/Sec, and return to normal operation within a few microseconds. Single Event Effect (SEE) testing of International Rectifier P-Channel RAD HARD HEXFETs has demonstrated virtual immunity to SEE failure. Since the P-Channel RAD HARD process utilizes International Rectifier's patented HEXFET technology, the user can expect the highest quality and reliability in the industry.

P-Channel RAD HARD HEXFET transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters. They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high-energy pulse circuits in space and weapons environments.

Product Summary

| Part Number | BV _{DSS} | R _{DS(on)} | I _D |
|-------------|-------------------|---------------------|----------------|
| IRHNA9064 | -60V | 0.055 Ω | -48A |

Features:

- Radiation Hardened up to 1×10^5 Rads (Si)
- Single Event Burnout (SEB) Hardened
- Single Event Gate Rupture (SEGR) Hardened
- Gamma Dot (Flash X-Ray) Hardened
- Neutron Tolerant
- Identical Pre- and Post-Electrical Test Conditions
- Repetitive Avalanche Rating
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Surface Mount
- Light-Weight

Absolute Maximum Ratings

Pre-Radiation

| | Parameter | IRHNA9064 | Units |
|---|--------------------------------------|-----------------|-------|
| I _D @ V _{GS} = -12V, T _C = 25°C | Continuous Drain Current | -48 | A |
| I _D @ V _{GS} = -12V, T _C = 100°C | Continuous Drain Current | -30 | |
| I _{DM} | Pulsed Drain Current ① | -192 | |
| P _D @ T _C = 25°C | Max. Power Dissipation | 300 | W |
| | Linear Derating Factor | 2.4 | W/K ⑤ |
| V _{GS} | Gate-to-Source Voltage | ± 20 | V |
| EAS | Single Pulse Avalanche Energy ② | 500 | mJ |
| I _{AR} | Avalanche Current ① | -48 | A |
| E _{AR} | Repetitive Avalanche Energy ① | 30 | mJ |
| dv/dt | Peak Diode Recovery dv/dt ③ | -5.5 | V/ns |
| T _J | Operating Junction | -55 to 150 | °C |
| T _{STG} | Storage Temperature Range | | |
| | Package Mounting Surface Temperature | 300 (For 5 sec) | |
| | Weight | 3.3 (typical) | g |



Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

| | Parameter | Min | Typ | Max | Units | Test Conditions |
|-------------------------------------|--|------|--------|-------|-------|--|
| BV _{DSS} | Drain-to-Source Breakdown Voltage | -60 | — | — | V | V _{GS} = 0 V, I _D = -1.0mA |
| ΔBV _{DSS} /ΔT _J | Temperature Coefficient of Breakdown Voltage | — | -0.048 | — | V/°C | Reference to 25°C, I _D = -1.0mA |
| R _{DS(on)} | Static Drain-to-Source On-State Resistance | — | — | 0.055 | Ω | V _{GS} = -12V, I _D = -30A ④ |
| | | — | — | 0.065 | | V _{GS} = -12V, I _D = -48A |
| V _{GS(th)} | Gate Threshold Voltage | -2.0 | — | -4.0 | V | V _{DS} = V _{GS} , I _D = -1.0mA |
| g _{fs} | Forward Transconductance | 16 | — | — | S (r) | V _{DS} > -15V, I _{DS} = -30A ④ |
| I _{DSS} | Zero Gate Voltage Drain Current | — | — | -25 | μA | V _{DS} = 0.8 x Max Rating, V _{GS} = 0V |
| | | — | — | -250 | | V _{DS} = 0.8 x Max Rating V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Leakage Forward | — | — | -100 | nA | V _{GS} = -20 V |
| I _{GSS} | Gate-to-Source Leakage Reverse | — | — | 100 | | V _{GS} = 20V |
| Q _g | Total Gate Charge | — | — | 260 | nC | V _{GS} = -12V, I _D = -48A |
| Q _{gs} | Gate-to-Source Charge | — | — | 60 | | V _{DS} = Max Rating x 0.5 |
| Q _{gd} | Gate-to-Drain ('Miller') Charge | — | — | 86 | | |
| t _{d(on)} | Turn-On Delay Time | — | — | 62 | ns | V _{DD} = -30V, I _D = -48A, R _G = 2.35Ω |
| t _r | Rise Time | — | — | 227 | | |
| t _{d(off)} | Turn-Off Delay Time | — | — | 200 | | |
| t _f | Fall Time | — | — | 115 | | |
| L _D | Internal Drain Inductance | — | 8.7 | — | nH | Measured from drain lead, 6mm (0.25 in) from package to center of die. |
| L _S | Internal Source Inductance | — | 8.7 | — | | Measured from source lead, 6mm (0.25 in) from package to source bonding pad. |
| C _{iss} | Input Capacitance | — | 7400 | — | pF | V _{GS} = 0V, V _{DS} = -25 V f = 1.0MHz |
| C _{oss} | Output Capacitance | — | 3200 | — | | |
| C _{rss} | Reverse Transfer Capacitance | — | 540 | — | | |

Source-Drain Diode Ratings and Characteristics

| | Parameter | Min | Typ | Max | Units | Test Conditions |
|-----------------|--|--|-----|------|-------|---|
| I _S | Continuous Source Current (Body Diode) | — | — | -48 | A | Modified MOSFET symbol showing the integral reverse p-n junction rectifier. |
| I _{SM} | Pulse Source Current (Body Diode) ① | — | — | -192 | | |
| V _{SD} | Diode Forward Voltage | — | — | -3.0 | V | T _j = 25°C, I _S = -48A, V _{GS} = 0V ④ |
| t _{rr} | Reverse Recovery Time | — | — | 480 | ns | T _j = 25°C, I _F = -48A, di/dt ≤ -100A/μs |
| Q _{RR} | Reverse Recovery Charge | — | — | 3.7 | μC | V _{DD} ≤ -50V ④ |
| t _{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D . | | | | |

Thermal Resistance

| | Parameter | Min | Typ | Max | Units | Test Conditions |
|----------------------|----------------------|-----|-----|------|-------|------------------------------------|
| R _{thJC} | Junction-to-Case | — | — | 0.42 | K/W ⑤ | Soldered to a copper-clad PC board |
| R _{thJ-PCB} | Junction-to-PC board | — | TBD | — | | |

① Limited by Pin diameter

Radiation Performance of P-Channel Rad Hard HEXFETs

International Rectifier Radiation Hardened HEXFETs are tested to verify their hardness capability. The hardness assurance program at International Rectifier uses two radiation environments.

Every manufacturing lot is tested in a low dose rate (total dose) environment per MIL-STD-750, test method 1019. International Rectifier has imposed a standard gate voltage of -12 volts per note 6 and a V_{DSS} bias condition equal to 80% of the device rated voltage per note 7. Pre- and post-radiation limits of the devices irradiated to 1×10^5 Rads (Si) are identical and are presented in Table 1. The values in Table 1 will be met for either of the two low dose rate test circuits that are used.

Both pre- and post-radiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison. It should be noted that at a radiation level of 1×10^5 Rads (Si) no changes in limits are specified in DC parameters.

High dose rate testing may be done on a special request basis using a dose rate up to 1×10^{12} Rads (Si)/Sec.

International Rectifier radiation hardened P-Channel HEXFETs are considered to be neutron-tolerant, as stated in MIL-PRF-19500 Group D. International Rectifier radiation hardened P-Channel HEXFETs have been characterized in heavy ion Single Event Effects (SEE) environments and the results are shown in Table 3.

Table 1. Low Dose Rate ⑥ ⑦

| Table 1. Low Dose Rate ⑥ ⑦ | | IRHNA9064 | | | |
|----------------------------|---|----------------|-------|-------|---|
| | Parameter | 100K Rads (Si) | | Units | Test Conditions ⑩ |
| | | Min | Max | | |
| BV _{DSS} | Drain-to-Source Breakdown Voltage | -60 | — | V | V _{GS} = 0V, I _D = -1.0mA |
| V _{GS(th)} | Gate Threshold Voltage ④ | -2.0 | -4.0 | | V _{GS} = V _{DS} , I _D = -1.0mA |
| I _{GSS} | Gate-to-Source Leakage Forward | — | -100 | nA | V _{GS} = -20V |
| I _{GSS} | Gate-to-Source Leakage Reverse | — | 100 | | V _{GS} = 20V |
| I _{DSS} | Zero Gate Voltage Drain Current | — | -25 | μA | V _{DS} =0.8 x Max Rating, V _{GS} =0V |
| R _{DS(on)1} | Static Drain-to-Source ④ On-State Resistance One | — | 0.055 | Ω | V _{GS} = -12V, I _D = -30A |
| V _{SD} | Diode Forward Voltage ④ | — | -3.0 | V | TC = 25°C, I _S = -48A, V _{GS} = 0V |

Table 2. High Dose Rate ⑧

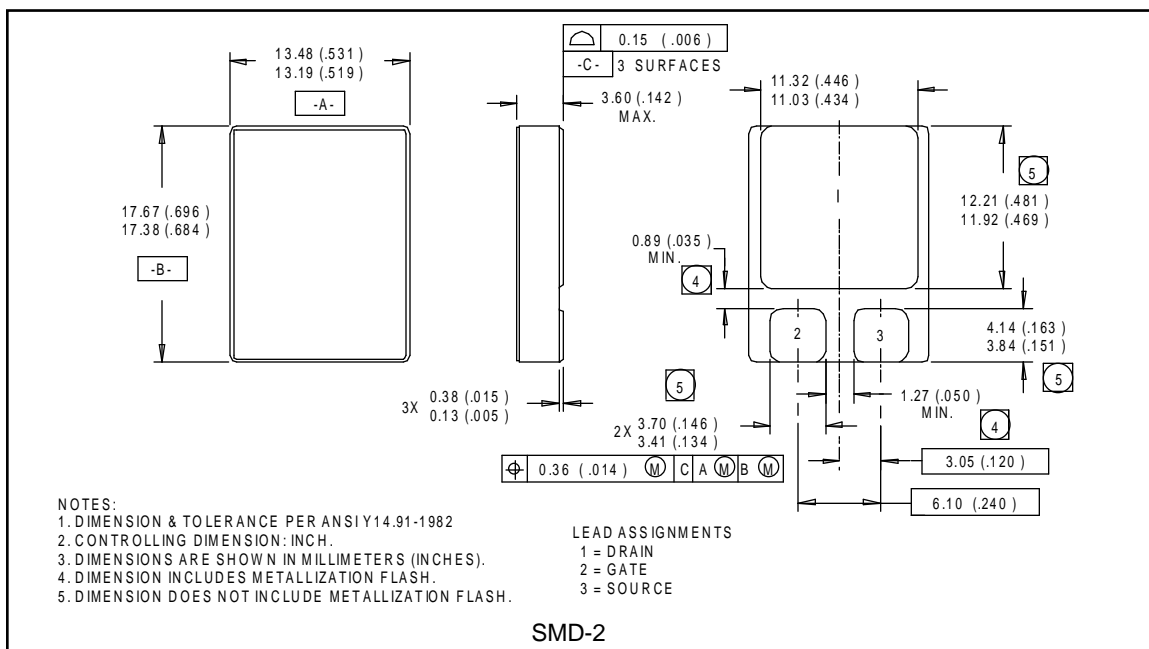
| | Parameter | 10 ¹¹ Rads (Si)/sec | | | 10 ¹² Rads (Si)/sec | | | Units | Test Conditions |
|-----------|-------------------------|--------------------------------|------|-----|--------------------------------|------|-----|--------------|--|
| | | Min | Typ | Max | Min | Typ | Max | | |
| V_{DSS} | Drain-to-Source Voltage | — | — | -48 | — | — | -48 | V | Applied drain-to-source voltage during gamma-dot |
| I_{PP} | | — | -100 | — | — | -100 | — | A | Peak radiation induced photo-current |
| di/dt | | — | -800 | — | — | -160 | — | A/ μ sec | Rate of rise of photo-current |
| L_1 | | 0.1 | — | — | 0.8 | — | — | μH | Circuit inductance required to limit di/dt |

Table 3. Single Event Effects ⑨

| Parameter | Typical | Units | Ion | LET (Si) (MeV/mg/cm ²) | Fluence (ions/cm ²) | Range (μm) | V_{DS} Bias (V) | V_{GS} Bias (V) |
|------------|---------|-------|-----|---------------------------------------|------------------------------------|----------------------|----------------------|----------------------|
| BV_{DSS} | -60 | V | Ni | 28 | 1×10^5 | ~41 | -60 | 5 |

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
Refer to current HEXFET reliability report.
- ② @ $V_{DD} = -25V$, Starting $T_J = 25^\circ C$,
 $E_{AS} = [0.5 * L * (I_L^2) * [BV_{DSS}/(BV_{DSS} - V_{DD})]]$
Peak $I_L = -48A$, $V_{GS} = -12V$, $25 \leq R_G \leq 200\Omega$
- ③ $I_{SD} \leq -48A$, $di/dt \leq -170 A/\mu s$,
 $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^\circ C$
Suggested $R_G = 2.35\Omega$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ $K/W = ^\circ C/W$
 $W/K = W/^\circ C$
- ⑥ **Total Dose Irradiation with V_{GS} Bias.**
-12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019.
- ⑦ **Total Dose Irradiation with V_{DS} Bias.**
 $V_{DS} = 0.8$ rated BV_{DSS} (pre-radiation) applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019.
- ⑧ This test is performed using a flash x-ray source operated in the e-beam mode (energy ~ 2.5 MeV), 30 nsec pulse.
- ⑨ Process characterized by independent laboratory.
- ⑩ All Pre-Radiation and Post-Radiation test conditions are **identical** to facilitate direct comparison for circuit applications.

Case Outline and Dimensions —



International
IOR Rectifier

WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331

EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

IR CANADA: 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 2Z8, Tel: (905) 475 1897

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR FAR EAST: K&H Bldg., 2F, 3-30-4 Nishi-Ikeburo 3-Chome, Toshima-Ki, Tokyo Japan 171 Tel: 81 3 3983 0086

IR SOUTHEAST ASIA: 315 Outram Road, #10-02 Tan Boon Liat Building, Singapore 0316 Tel: 65 221 8371

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